

2SC5379

Silicon NPN epitaxial planer type

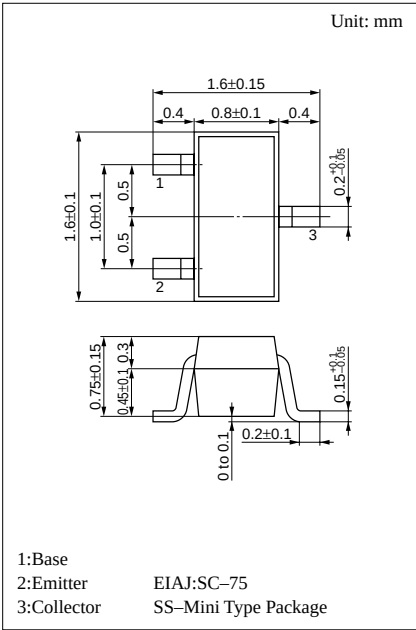
For low-voltage low-noise high-frequency oscillation

Features

- Low noise figure NF.
- High gain.
- High transition frequency f_T .
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	80	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 ~ +125	°C



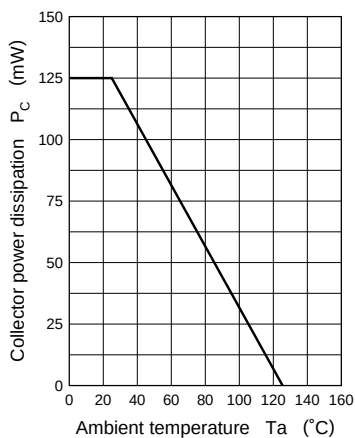
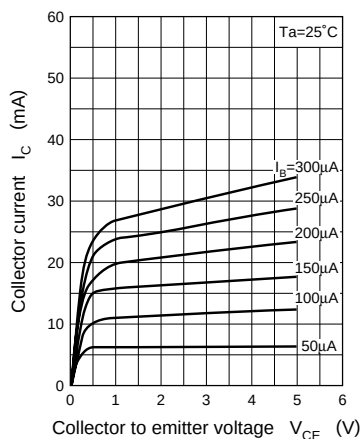
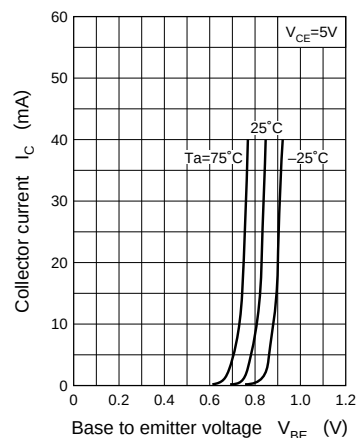
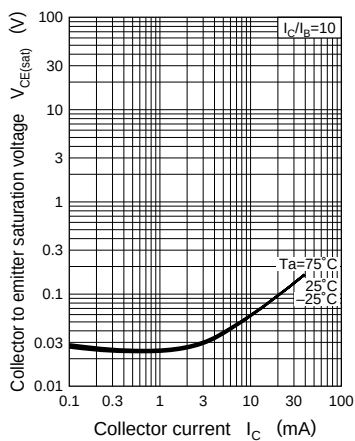
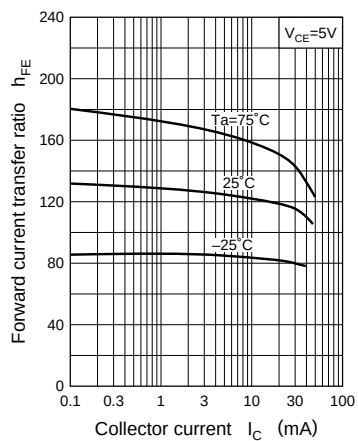
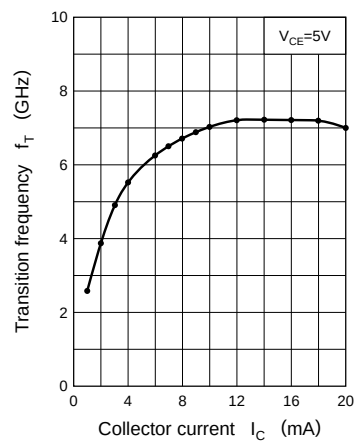
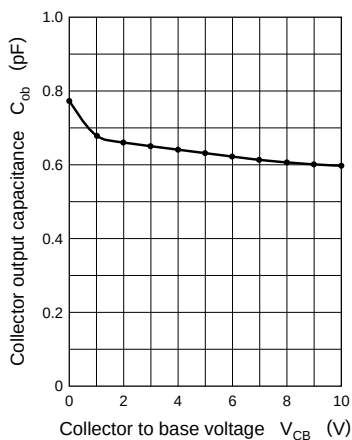
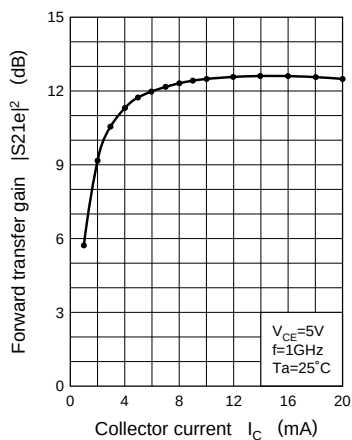
Marking symbol : HT

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 10V, I_E = 0$			1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 1V, I_C = 0$			1	μA
Forward current transfer ratio	h_{FE}^*	$V_{CE} = 5V, I_C = 10mA$	80		200	
Transition frequency	f_T	$V_{CE} = 5V, I_C = 10mA, f = 2GHz$		7.0		GHz
Collector output capacitance	C_{ob}	$V_{CB} = 5V, I_E = 0, f = 1MHz$		0.6	1.0	pF
Foward transfer gain	$ S_{21e} ^2$	$V_{CE} = 5V, I_C = 10mA, f = 1GHz$	8.5	11.0		dB
Noise figure	NF	$V_{CE} = 5V, I_C = 3mA, f = 1GHz$		1.6	2	dB

* h_{FE} Rank classification

Rank	Q	R	S
h_{FE}	80 ~ 115	95 ~ 155	135 ~ 200
Marking Symbol	HTQ	HTR	HTS

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_C$  $C_{ob} - V_{CB}$  $|S_{21e}|^2 - I_C$  $NF - I_C$ 